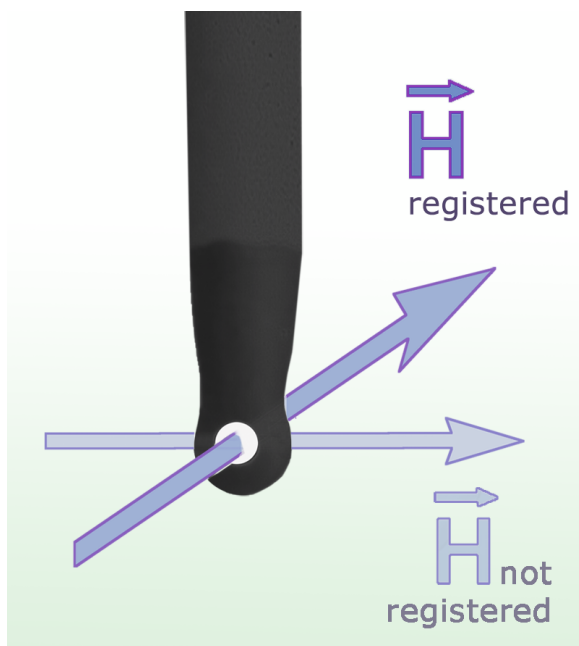


# RF-R 3-2

H-Field Probe 30 MHz up to 3 GHz



## Short description

The RF-R 3-2 near-field probe is used for the high-resolution measurement of RF magnetic fields directly on an assembly e.g. in range around pins and IC cases, conducting paths, decoupling capacitor and EMC components.

The RF-R 3-2 is a passive near-field probe. It has the same basic construction as the RF-R 50-1 and RF-R 500-1 probes. However, the resolution of RF-R 3-2 is much higher. The H-field probe is designed to be used very close to the components and where high magnetic field strength occurs. It is not suitable for measurements from great distances, which can be done using the RF-R 400-1 and RF-R 50-1 probes. The near-field probe is small and handy. It has a current attenuating sheath and its upper side is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field probe does not have an internal terminating resistance of 50  $\Omega$ .

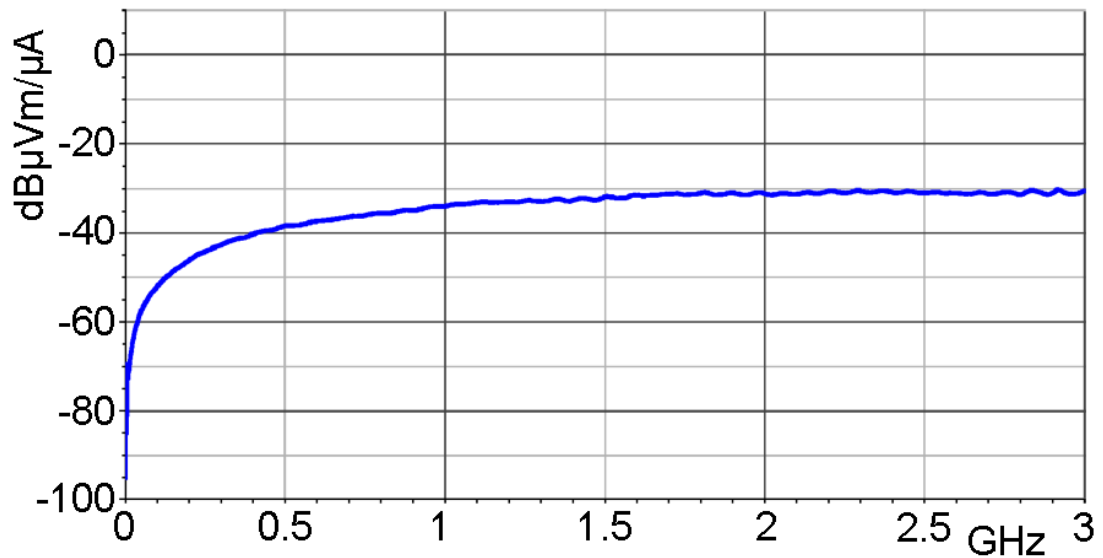
## Technical parameters

Frequency range	30 MHz ... 3 GHz
Resolution	$\approx 1$ mm
Probe head dimensions	$\varnothing \approx 3$ mm
Connector - output	SMB, male, jack
Weight	15 g

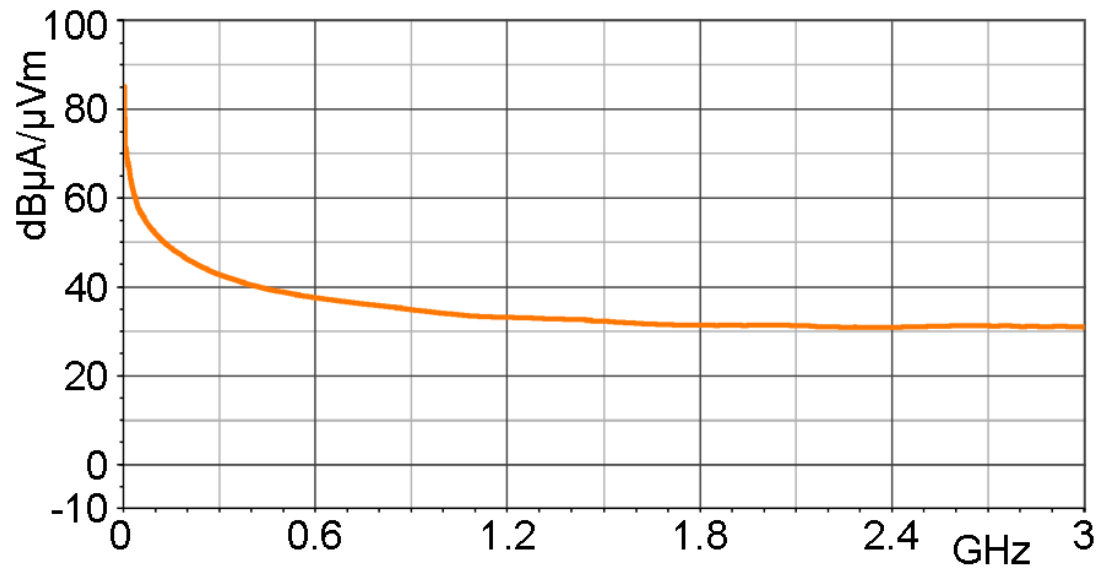
# RF-R 3-2

H-Field Probe 30 MHz up to 3 GHz

Frequency response [dB $\mu$ V] / [dB $\mu$ A/m]



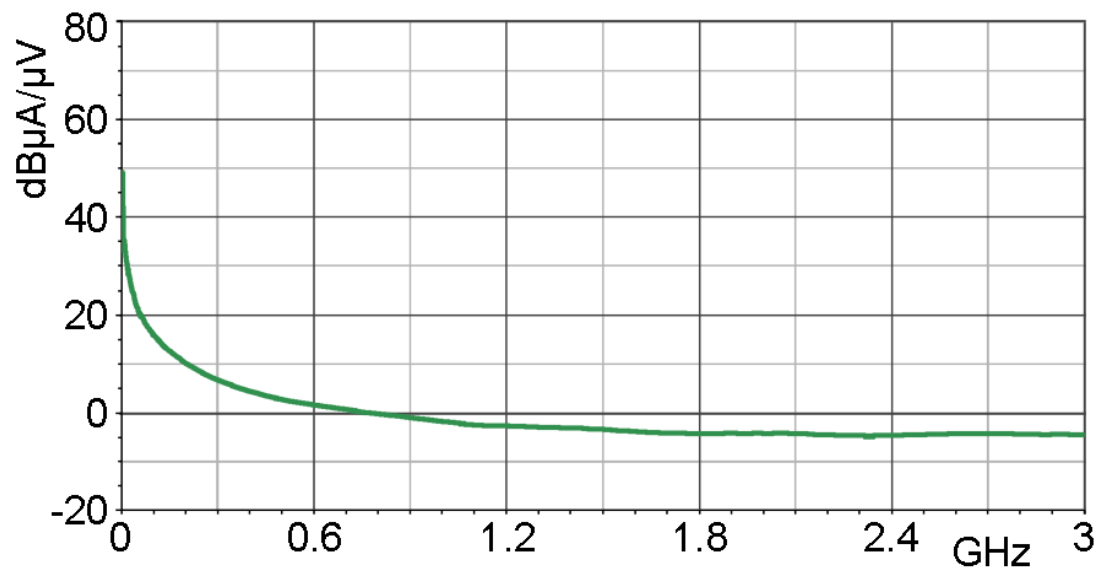
H-field correction curve [dB $\mu$ A/m] / [dB $\mu$ V]



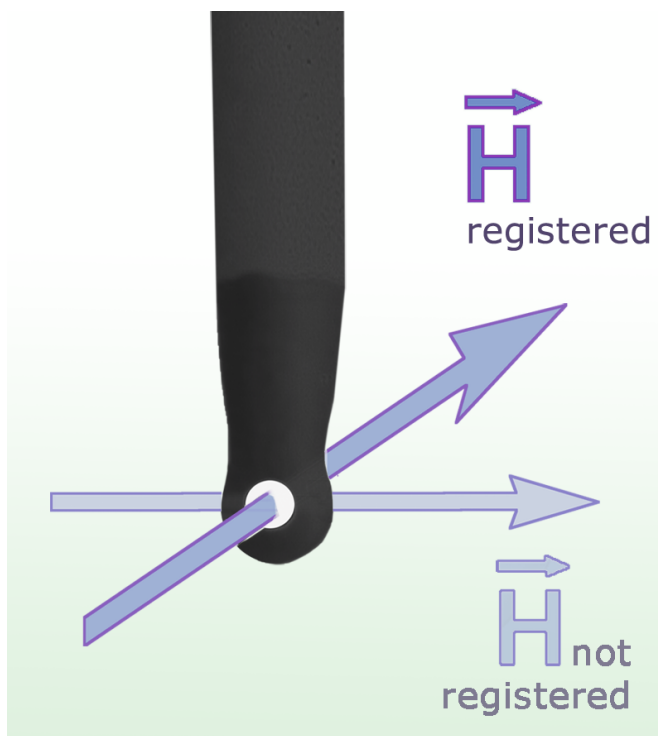
## RF-R 3-2

H-Field Probe 30 MHz up to 3 GHz

Current correction curve [dB $\mu$ A] / [dB $\mu$ V]



Measuring principles



# RF-R 3-2

H-Field Probe 30 MHz up to 3 GHz

**LANGER**  
EMV-Technik

Probe head

